Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional blocking voltage capability, high current inrush capability and high thermal cycling performance.

2. Features and benefits

- AC power control
- · High bidirectional blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High junction operating temperature capability (T_{j(max)} = 150 °C)
- Package meets UL94V0 flammability requirement
- · Package is RoHS compliant
- IEC 61000-4-4 fast transient

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation
- High junction operating temperature capability (T_{i(max)} = 150 °C)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute r	maximum rating			
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 128°C; Fig. 1; Fig. 2; Fig. 3	25	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5	300	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$	330	А
T _j	junction temperature		150	°C

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit					
Static cha	Static characteristics											
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		1.5	-	10	mA					
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	-	60	mA					
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.10	1.50	V					
Dynamic o	haracteristics											
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		80	-	-	V/µs					

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A 🕌 K
2	Α	anode	}	G sym037
3	G	gate		symoor
mb	A	mounting base; connect to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT145-800RT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
V_{RRM}	repetitive peak reverse voltage		800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 128°C;	16	Α
$I_{T(RMS)}$	RMS on-state current	half sine wave; T _{mb} ≤ 128°C; Fig. 1; Fig. 2; Fig. 3	25	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	300	А
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	330	А
l ² t	I ² t for fusing	t _p = 10ms; sine wave	450	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20mA	200	A/µs
I _{GM}	peak gate current		5	Α
V_{GM}	peak gate voltage		5	V
P_{GM}	peak gate power		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

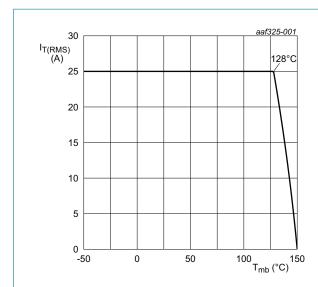
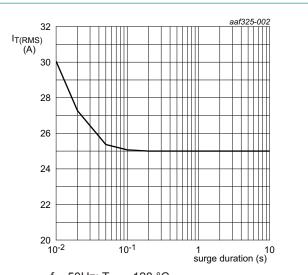


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50Hz; T_{mb} = 128 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values

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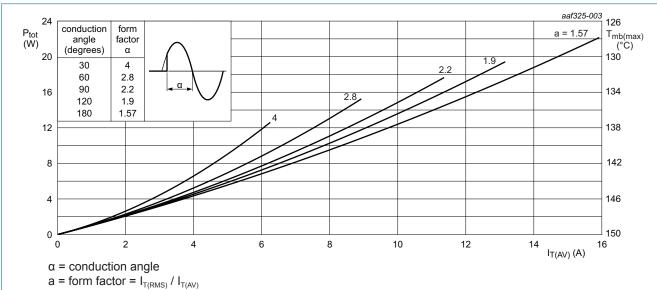


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

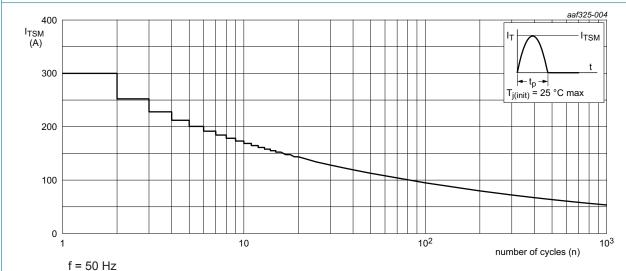
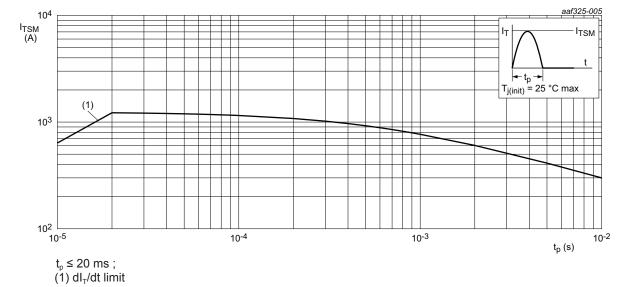


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

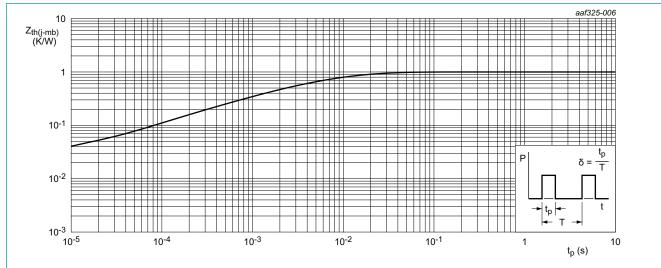


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6 Characteristics

able 6. Cil	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I_{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	1.5	-	10	mA
I _L	latching current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	-	80	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.10	1.50	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.6	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	2	mA
I _R	reverse current	V _D = 800 V; T _j = 150 °C	-	-	2	mA
Dynamic c	haracteristics				•	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	80	-	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ mA};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}$		2	-	μs
t _q	commutated turn-off time	V_{DM} = 536 V; T_j = 125 °C; I_{TM} = 50 A; V_R = 25 V; dI_T/dt = 30 A/µs; dV_D/dt = 50 V/µs		70	-	μs

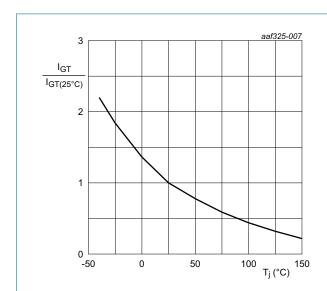


Fig. 7. Normalized gate trigger current as a function of junction temperature

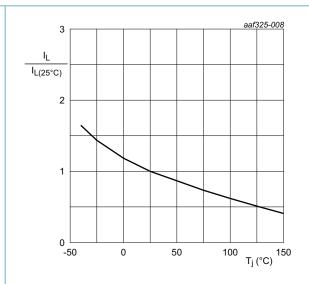


Fig. 8. Normalized latching current as a function of junction temperature

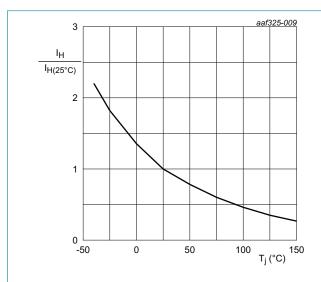
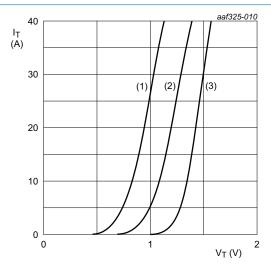


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 0.987 V; R_s = 0.0103 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

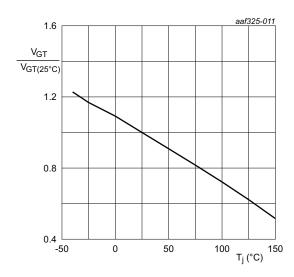
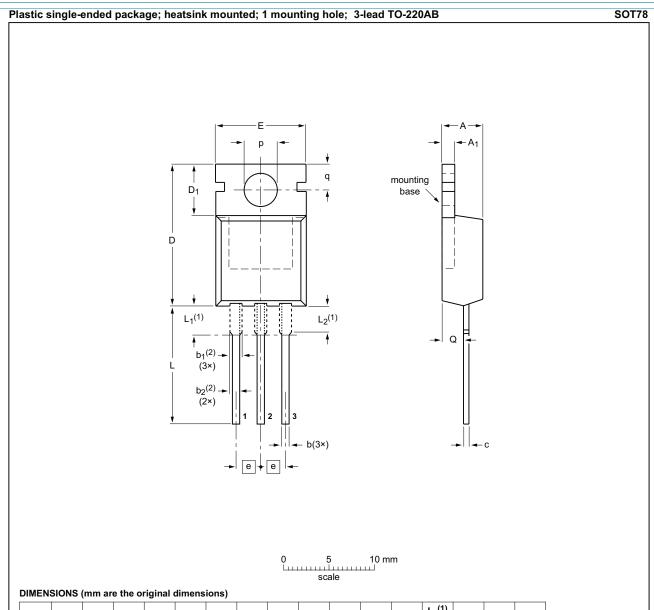


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline



UNIT	A	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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